



TF252TH — N-channel Silicon Junction FET Electret Condenser Microphone Applications

Features

- High gain : $G_V=1.0\text{dB typ}$ ($V_{CC}=2\text{V}$, $R_L=2.2\text{k}\Omega$, $C_{in}=5\text{pF}$, $V_{IN}=10\text{mV}$, $f=1\text{kHz}$).
- Ultrasmall package facilitates miniaturization in end products.
- Best suited for use in Electret Condenser Microphone for audio equipments and telephones.
- Excellent voltage characteristics.
- Excellent transient characteristics.
- Adoption of FBET process.
- Halogen free compliance.

Specifications

Absolute Maximum Ratings at $T_a=25^\circ\text{C}$

Parameter	Symbol	Conditions	Ratings	Unit
Gate-to-Drain Voltage	V_{GDO}		-20	V
Gate Current	I_G		10	mA
Drain Current	I_D		1	mA
Allowable Power Dissipation	PD		100	mW
Junction Temperature	T_J		150	$^\circ\text{C}$
Storage Temperature	T_{stg}		-55 to +150	$^\circ\text{C}$

Marking: D

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70407GB TI IM TC-00000796 No. A0842-1/4

TF252TH

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Gate-to-Drain Breakdown Voltage	$V_{(BR)GDO}$	$I_G = -100\mu A$	-20			V
Cutoff Voltage	$V_{GS(off)}$	$V_{DS} = 2V, I_D = 1\mu A$	-0.1	-0.4	-1.0	V
Zero-Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 2V, V_{GS} = 0V$	140*		350*	μA
Forward Transfer Admittance	$ y_{fs} $	$V_{DS} = 2V, V_{GS} = 0V, f = 1kHz$	0.8	1.4		mS
Input Capacitance	C_{iss}	$V_{DS} = 2V, V_{GS} = 0V, f = 1MHz$		3.1		pF
Reverse Transfer Capacitance	C_{rss}	$V_{DS} = 2V, V_{GS} = 0V, f = 1MHz$		0.95		pF
[Ta=25°C, VCC=2V, RL=2.2kΩ, Cin=5pF, See specified Test Circuit.]						
Voltage Gain	G_V	$V_{IN} = 10mV, f = 1kHz$		1.0		dB
Reduced Voltage Characteristic	ΔG_V	$V_{IN} = 10mV, f = 1kHz, V_{CC} = 2.0 \rightarrow 1.5V$		-0.6	-2.0	dB
Frequency Characteristic	$\Delta G_V f$	$f = 1kHz \text{ to } 110Hz$			-1.0	dB
Total Harmonic Distortion	THD	$V_{IN} = 30mV, f = 1kHz$		0.65		%
Output Noise Voltage	V_{NO}	$V_{IN} = 0V, A \text{ curve}$		-106	-102	dB

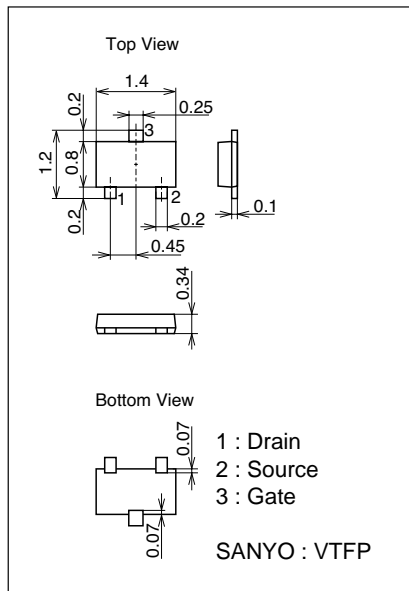
* : The TF252TH is classified by I_{DSS} as follows : (unit : μA)

Rank	4	5
I_{DSS}	140 to 240	210 to 350

Package Dimensions

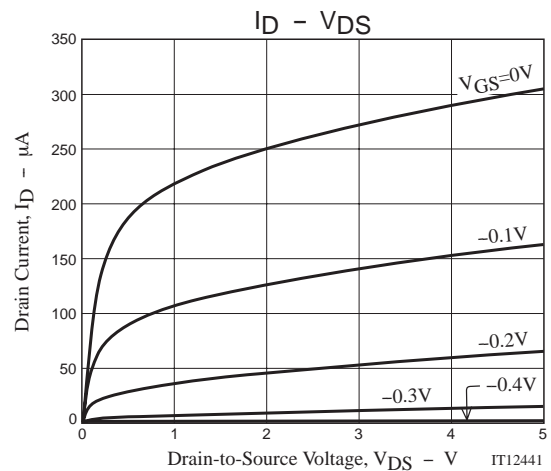
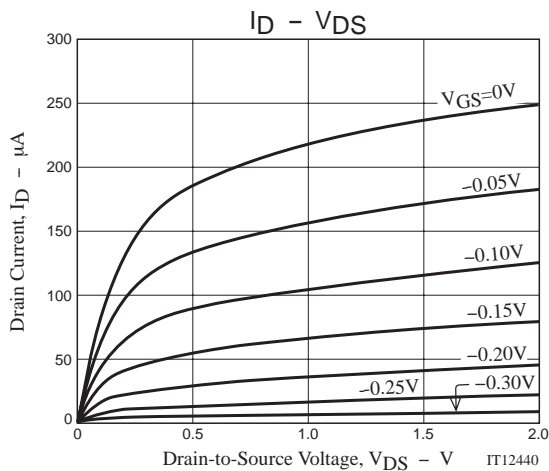
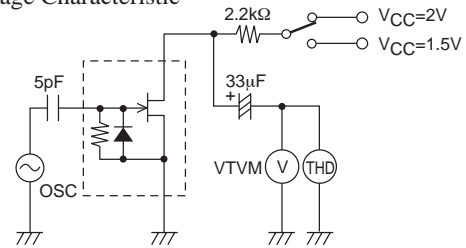
unit : mm (typ)

7031-001

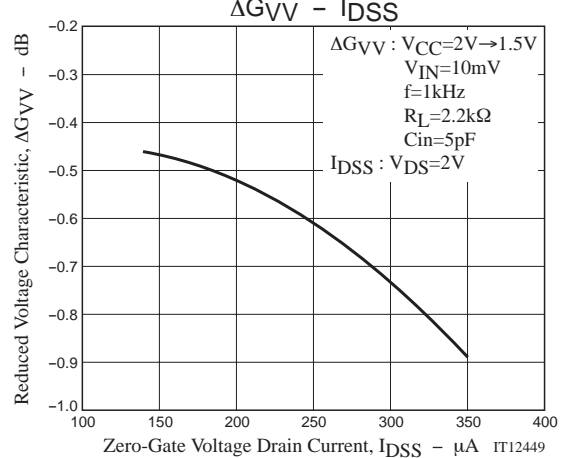
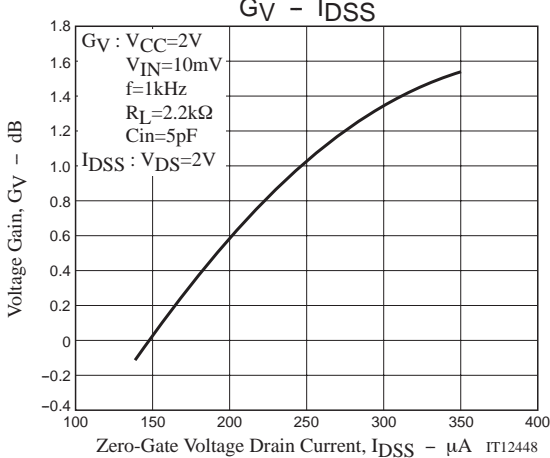
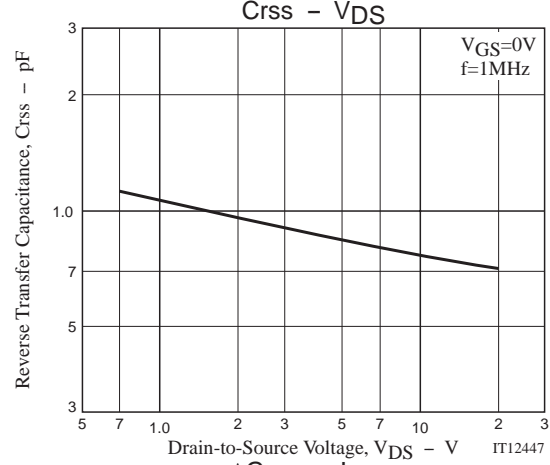
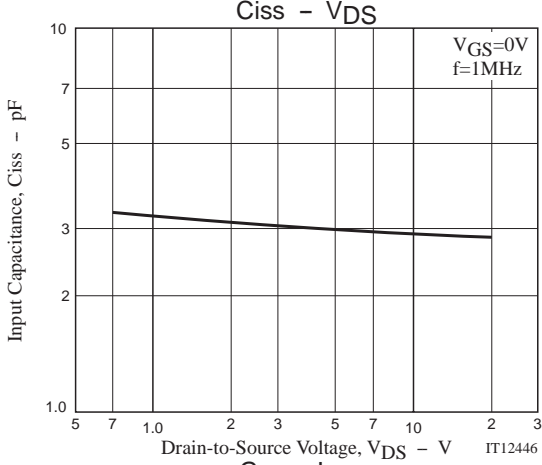
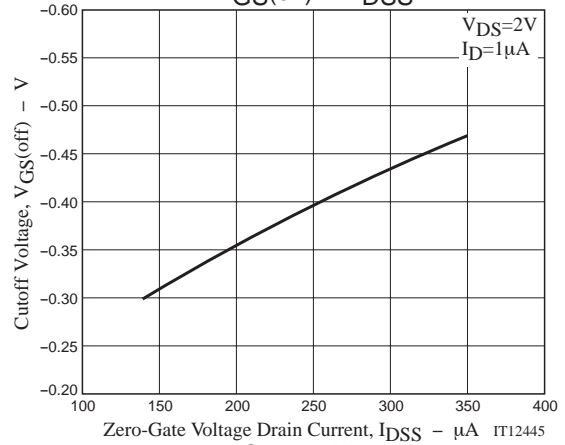
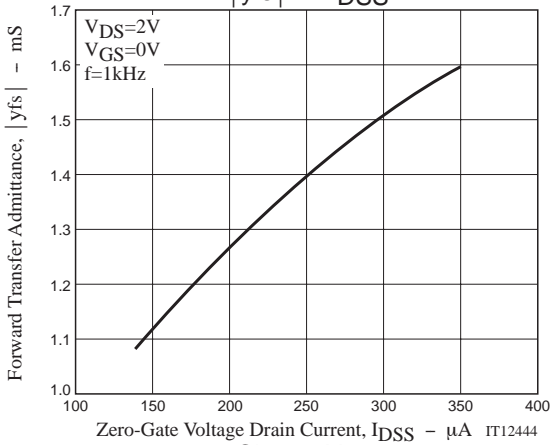
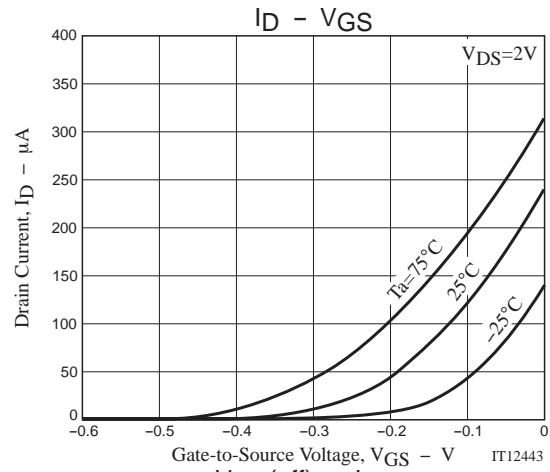
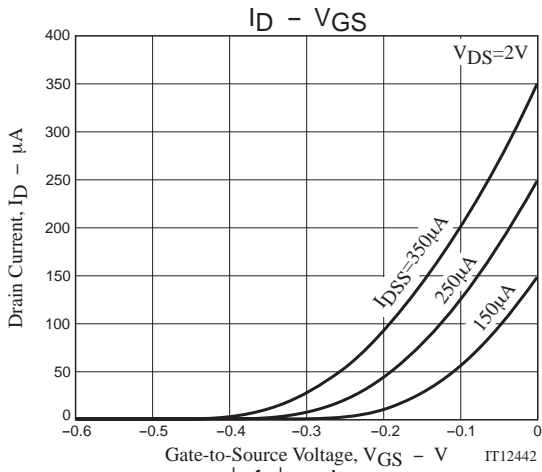


Test Circuit

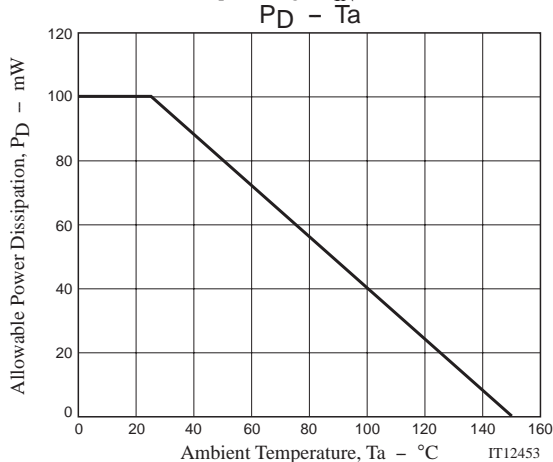
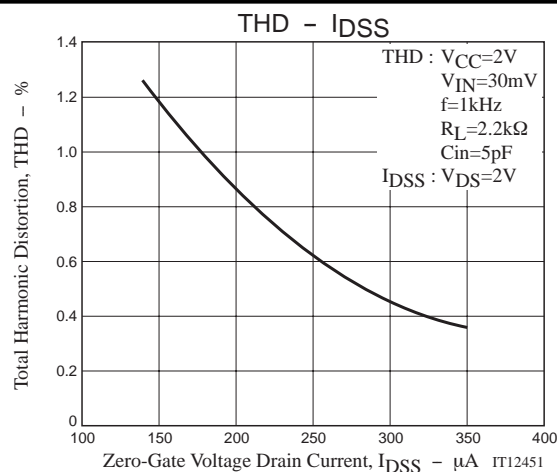
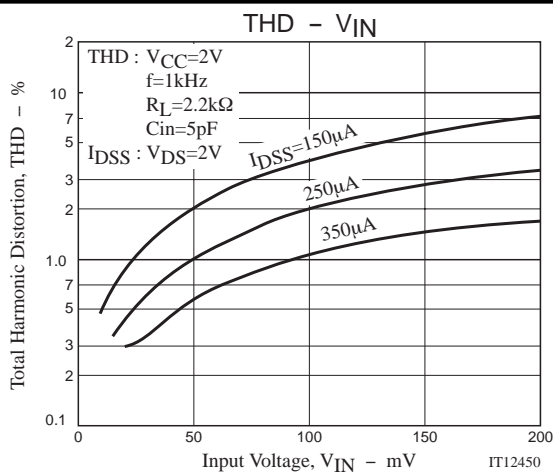
Voltage gain
Frequency Characteristic
Distortion
Reduced Voltage Characteristic



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